

Final datasheet

High speed and low saturation voltage 750 V TRENCHSTOP™ IGBT7 technology co-packed with soft and fast recovery Emitter Controlled 7 diode

Features

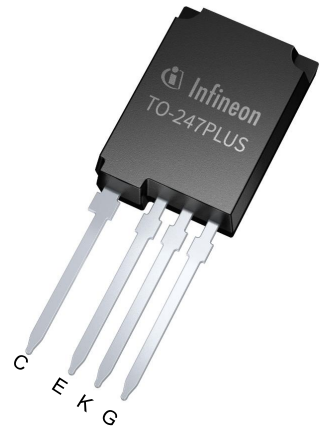
- $V_{CE} = 750\text{ V}$
- $I_C = 150\text{ A}$
- Low switching losses
- Very low collector-emitter saturation voltage V_{CEsat}
- Very soft, fast recovery antiparallel diode
- Smooth switching behavior
- Humidity robustness
- Optimized for hard switching, two- and three-level topologies
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

Potential applications

- Industrial UPS
- EV Charging
- String inverter
- Energy storage systems (ESS)

Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

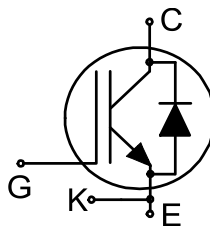


- Lead-free
- Green
- Halogen-free
- RoHS

Description

Pin definition:

- Pin C & backside – Collector
- Pin E – Emitter
- Pin K – Kelvin emitter
- Pin G – Gate



Type	Package	Marking
IKY150N75EH7	PG-TO247-4-U10	K150GEH7

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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.19	0.24	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.26	0.33	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25\text{ °C}$	750	V	
DC collector current, limited by T_{vjmax}	I_C	limited by bondwire	$T_c = 25\text{ °C}$	160	A
			$T_c = 100\text{ °C}$	160	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}		600	A	
Turn-off safe operating area		$V_{CE} \leq 750\text{ V}$, $t_p \leq 1\text{ }\mu\text{s}$, $T_{vj} \leq 175\text{ °C}$	600	A	
Gate-emitter voltage	V_{GE}		± 20	V	
Transient gate-emitter voltage	V_{GE}	$t_p \leq 10\text{ }\mu\text{s}$, $D < 0.01$	± 30	V	
Power dissipation	P_{tot}		$T_c = 25\text{ °C}$	625	W
			$T_c = 100\text{ °C}$	313	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 150\text{ A}$, $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.45	1.75	V
			$T_{vj} = 175\text{ °C}$	1.75		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Gate-emitter threshold voltage	V_{GEth}	$I_C = 1.32 \text{ mA}$, $V_{CE} = V_{GE}$	3.2	4	4.8	V
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 750 \text{ V}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$		50	μA
			$T_{vj} = 175 \text{ °C}$		4500	
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = 20 \text{ V}$			100	nA
Transconductance	g_{fs}	$I_C = 150 \text{ A}$, $V_{CE} = 20 \text{ V}$		186		S
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 100 \text{ kHz}$		7950		pF
Output capacitance	C_{oes}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 100 \text{ kHz}$		222		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 100 \text{ kHz}$		30		pF
Gate charge	Q_G	$V_{CC} = 600 \text{ V}$, $I_C = 150 \text{ A}$, $V_{GE} = 15 \text{ V}$		300		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_{G(on)} = 10 \text{ }\Omega$, $R_{G(off)} = 10 \text{ }\Omega$	$T_{vj} = 25 \text{ °C}$, $I_C = 150 \text{ A}$		43	ns
			$T_{vj} = 175 \text{ °C}$, $I_C = 150 \text{ A}$		41	
Rise time (inductive load)	t_r	$V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_{G(on)} = 10 \text{ }\Omega$, $R_{G(off)} = 10 \text{ }\Omega$	$T_{vj} = 25 \text{ °C}$, $I_C = 150 \text{ A}$		23	ns
			$T_{vj} = 175 \text{ °C}$, $I_C = 150 \text{ A}$		28	
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_{G(on)} = 10 \text{ }\Omega$, $R_{G(off)} = 10 \text{ }\Omega$	$T_{vj} = 25 \text{ °C}$, $I_C = 150 \text{ A}$		324	ns
			$T_{vj} = 175 \text{ °C}$, $I_C = 150 \text{ A}$		363	
Fall time (inductive load)	t_f	$V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_{G(on)} = 10 \text{ }\Omega$, $R_{G(off)} = 10 \text{ }\Omega$	$T_{vj} = 25 \text{ °C}$, $I_C = 150 \text{ A}$		23	ns
			$T_{vj} = 175 \text{ °C}$, $I_C = 150 \text{ A}$		59	
Turn-on energy	E_{on}	$V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_{G(on)} = 10 \text{ }\Omega$, $R_{G(off)} = 10 \text{ }\Omega$	$T_{vj} = 25 \text{ °C}$, $I_C = 150 \text{ A}$		3	mJ
			$T_{vj} = 175 \text{ °C}$, $I_C = 150 \text{ A}$		4	
Turn-off energy	E_{off}	$V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_{G(on)} = 10 \text{ }\Omega$, $R_{G(off)} = 10 \text{ }\Omega$	$T_{vj} = 25 \text{ °C}$, $I_C = 150 \text{ A}$		2.5	mJ
			$T_{vj} = 175 \text{ °C}$, $I_C = 150 \text{ A}$		4	

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Total switching energy	E_{ts}	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 150\text{ A}$		5.4	mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 150\text{ A}$		8	
Operating junction temperature	T_{vj}		-40		175	$^\circ\text{C}$

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Diode forward current, limited by T_{vjmax}	I_F	limited by bondwire	$T_c = 25\text{ }^\circ\text{C}$	160	A
			$T_c = 100\text{ }^\circ\text{C}$	149	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}		600	A	
Power dissipation	P_{tot}		$T_c = 25\text{ }^\circ\text{C}$	455	W
			$T_c = 100\text{ }^\circ\text{C}$	227	

Table 5 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 150\text{ A}$	$T_{vj} = 25\text{ }^\circ\text{C}$	1.65	2	V
			$T_{vj} = 175\text{ }^\circ\text{C}$	1.6		
Diode reverse recovery time	t_{rr}	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 150\text{ A}$	102		ns
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 150\text{ A}$	181		
Diode reverse recovery charge	Q_{rr}	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 150\text{ A}$	4.1		μC
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 150\text{ A}$	11.9		
Diode peak reverse recovery current	I_{rrm}	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 150\text{ A}$	82.8		A
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 150\text{ A}$	132.5		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Diode peak rate of fall of reverse recovery current	di_{rr}/dt	$V_R = 400 \text{ V}, R_{G(on)} = 10 \text{ } \Omega$	$T_{vj} = 25 \text{ } ^\circ\text{C},$ $I_F = 150 \text{ A}$		-1010		A/ μs
			$T_{vj} = 175 \text{ } ^\circ\text{C},$ $I_F = 150 \text{ A}$		-897		
Reverse recovery energy	E_{rec}	$V_R = 400 \text{ V}, R_{G(on)} = 10 \text{ } \Omega$	$T_{vj} = 25 \text{ } ^\circ\text{C},$ $I_F = 150 \text{ A}$		0.98		mJ
			$T_{vj} = 175 \text{ } ^\circ\text{C},$ $I_F = 150 \text{ A}$		3.35		
Operating junction temperature	T_{vj}			-40		175	$^\circ\text{C}$

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

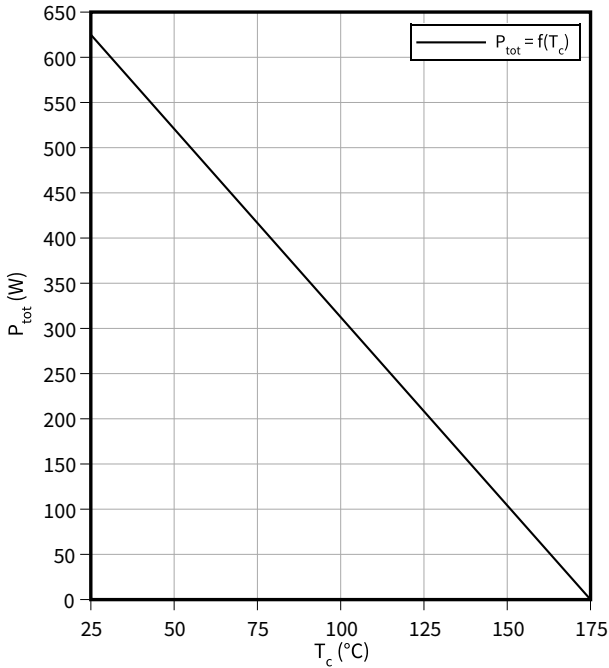
Electrical Characteristic, at $T_{vj} = 25 \text{ } ^\circ\text{C}$, unless otherwise specified.

Dynamic test circuit, parasitic inductance $L_\sigma = 15 \text{ nH}$, parasitic capacitor $C_\sigma = 16 \text{ pF}$ from Fig. E. Energy losses include "tail" and diode reverse recovery.

4 Characteristics diagrams

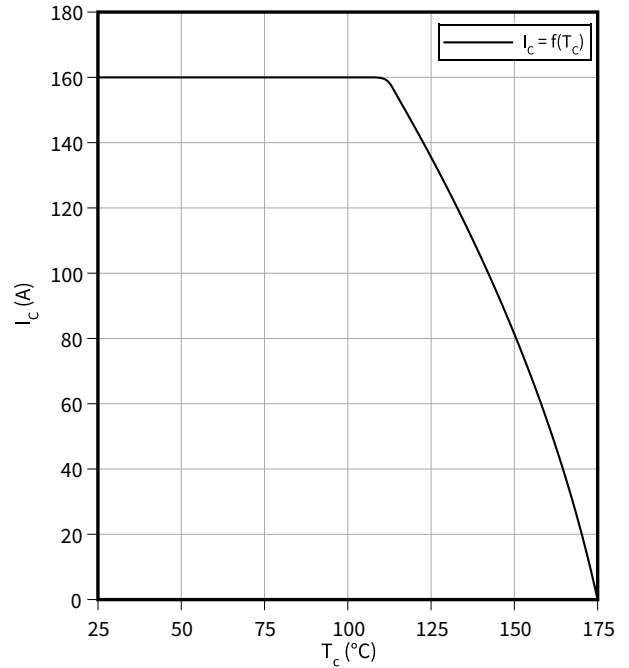
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$
 $T_{vj} \leq 175\text{ °C}$



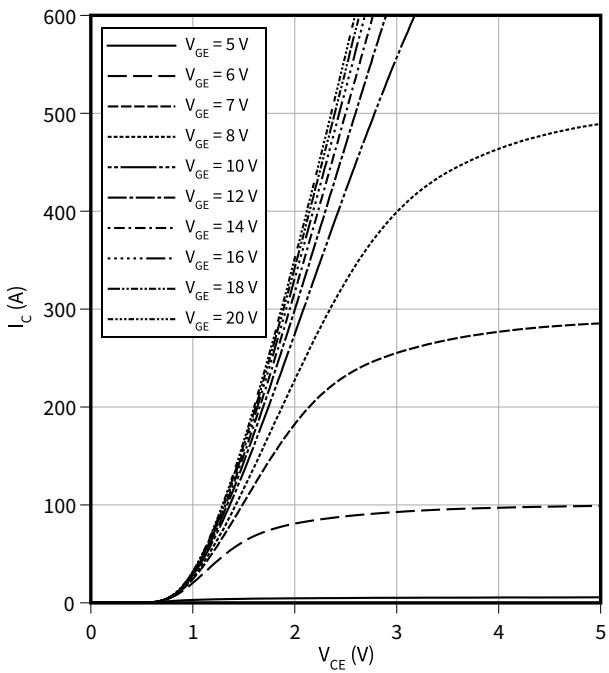
Collector current as a function of case temperature

$I_C = f(T_c)$
 $T_{vj} \leq 175\text{ °C}, V_{GE} = 15\text{ V}$



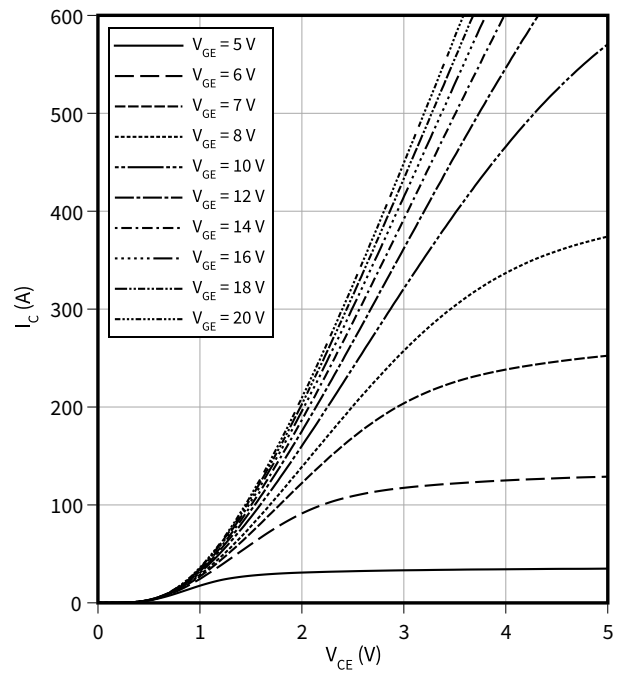
Typical output characteristic

$I_C = f(V_{CE})$
 $T_{vj} = 25\text{ °C}$



Typical output characteristic

$I_C = f(V_{CE})$
 $T_{vj} = 175\text{ °C}$

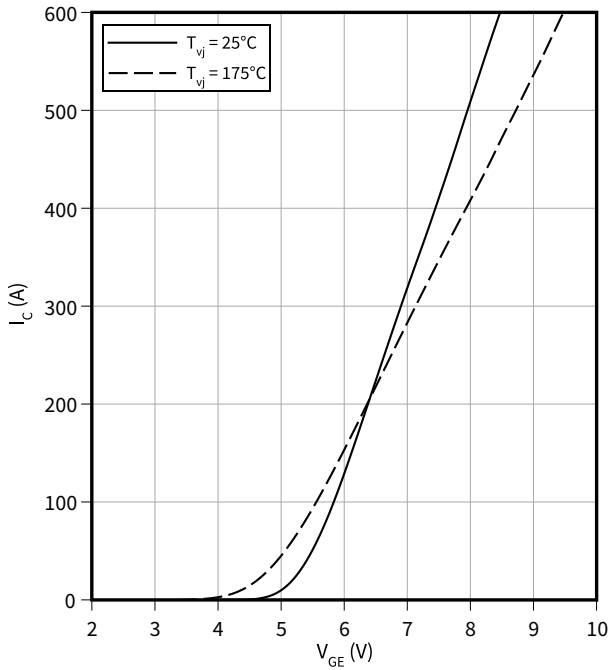


4 Characteristics diagrams

Typical transfer characteristic

$I_C = f(V_{GE})$

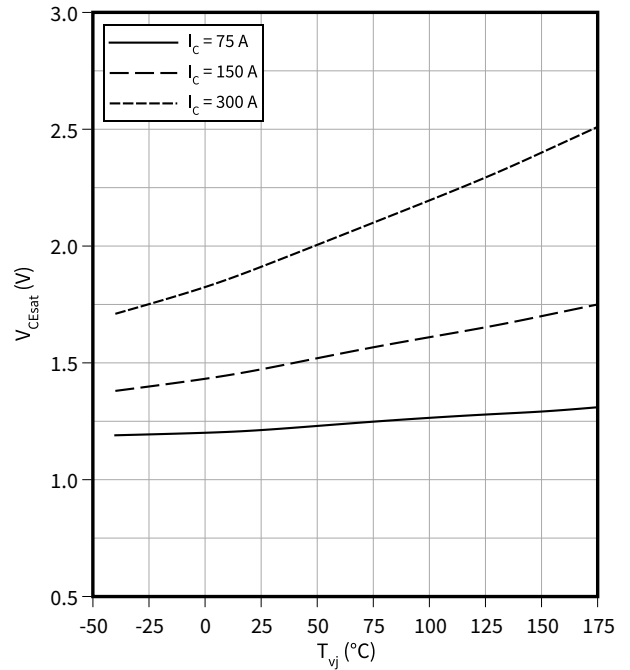
$V_{CE} = 20\text{ V}$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

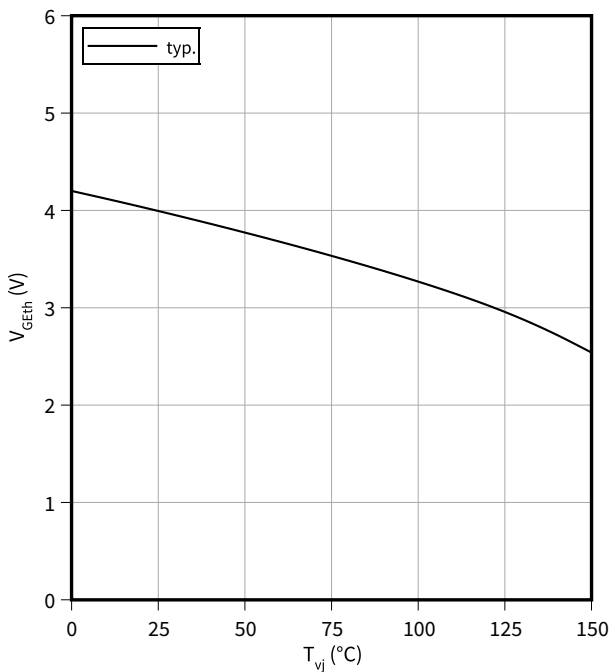
$V_{GE} = 15\text{ V}$



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

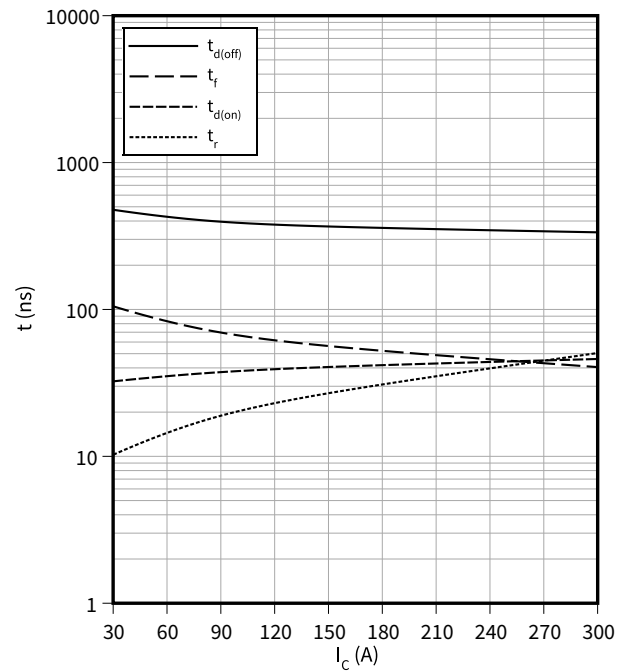
$I_C = 1.32\text{ mA}$



Typical switching times as a function of collector current

$t = f(I_C)$

$V_{CC} = 400\text{ V}, T_{vj} = 175^\circ\text{C}, V_{GE} = 0/15\text{ V}, R_G = 10\ \Omega$

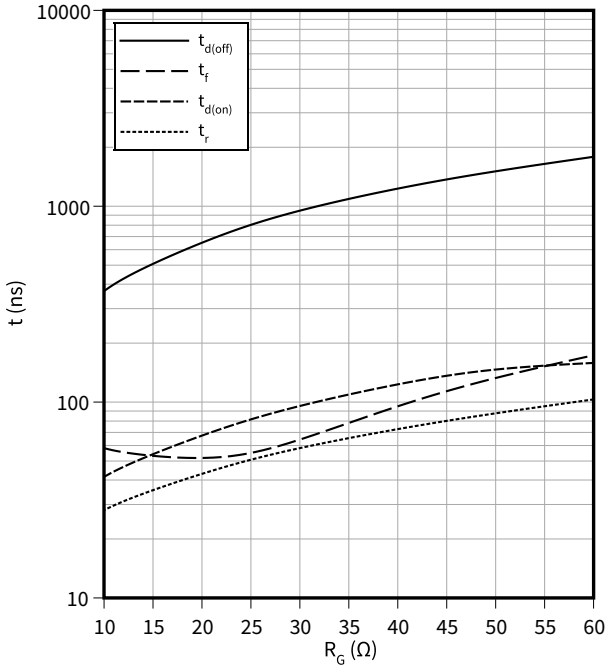


4 Characteristics diagrams

Typical switching times as a function of gate resistor

$t = f(R_G)$

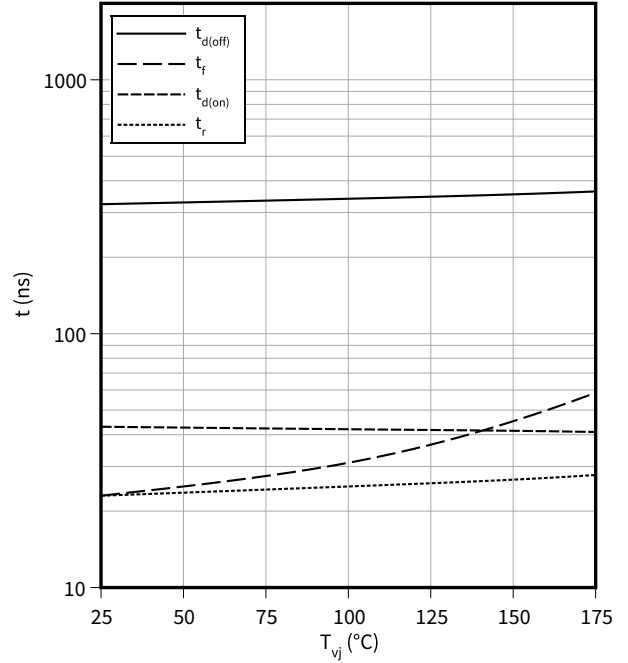
$I_C = 150 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

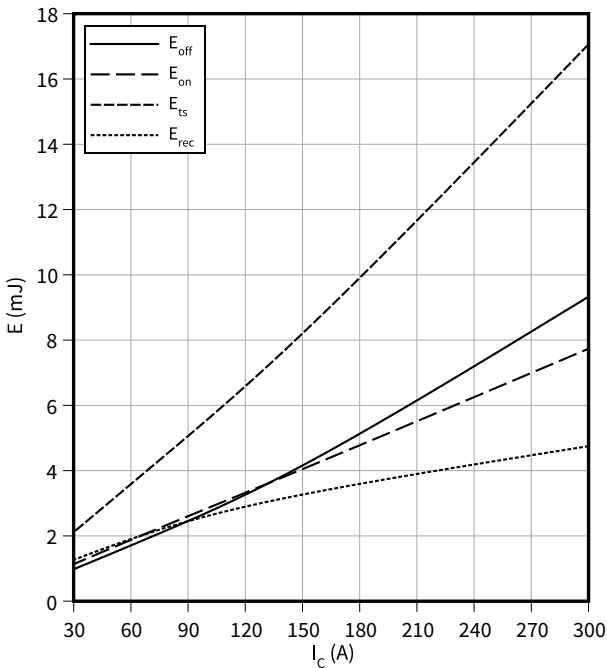
$I_C = 150 \text{ A}, V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 10 \text{ } \Omega$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

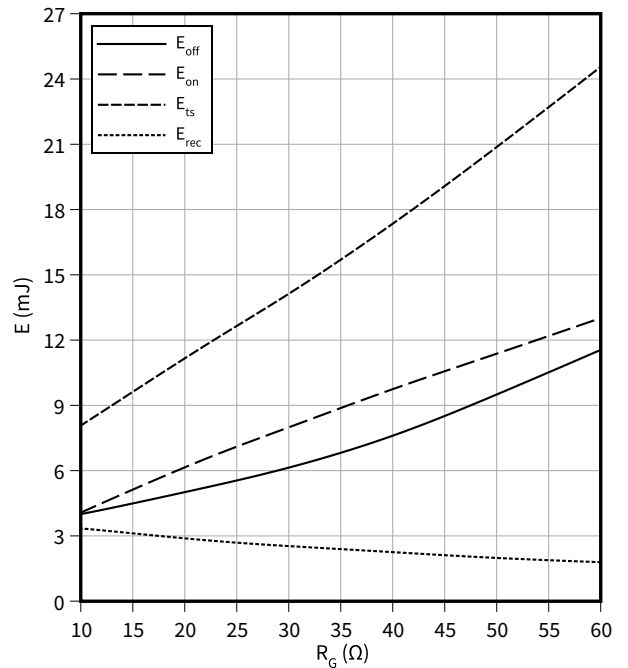
$V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}, R_G = 10 \text{ } \Omega$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

$I_C = 150 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$

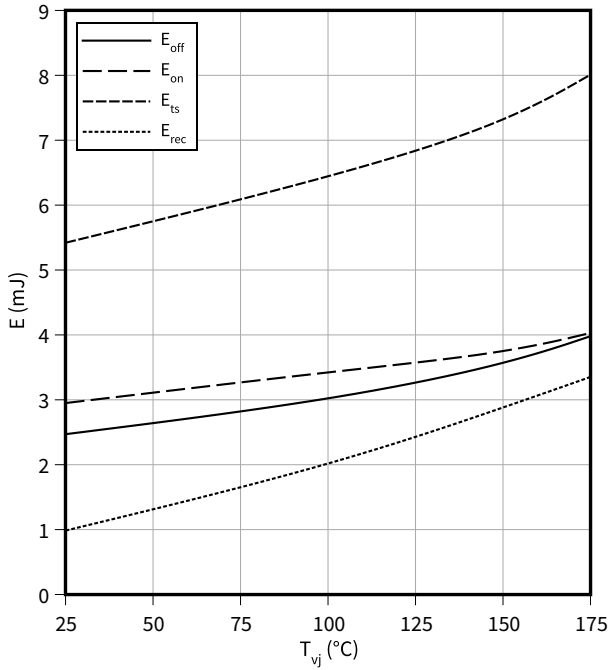


4 Characteristics diagrams

Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

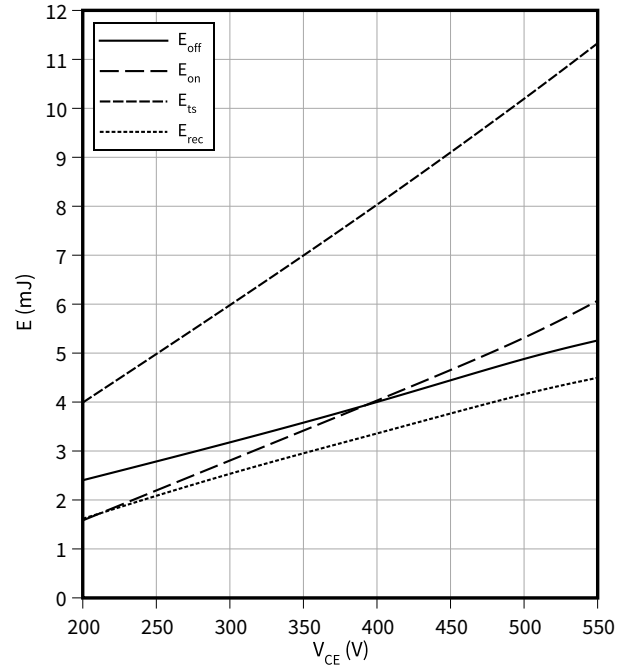
$I_C = 150\text{ A}, V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_G = 10\ \Omega$



Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$

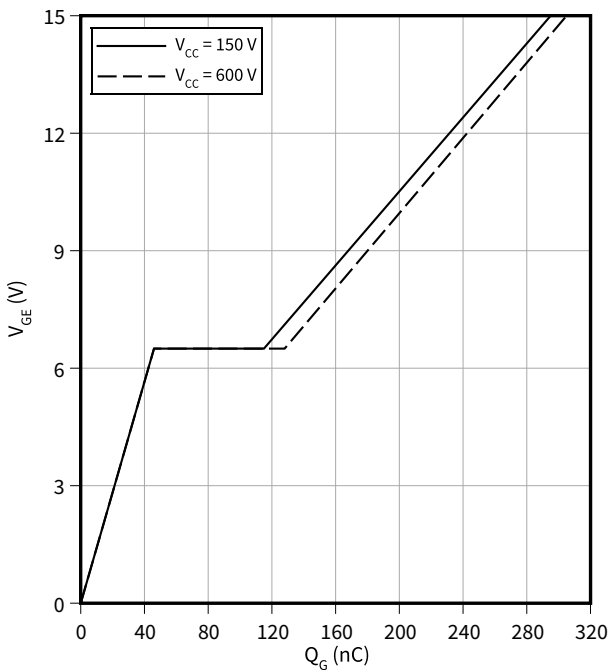
$I_C = 150\text{ A}, T_{vj} = 175\text{ °C}, V_{GE} = 0/15\text{ V}, R_G = 10\ \Omega$



Typical gate charge

$V_{GE} = f(Q_G)$

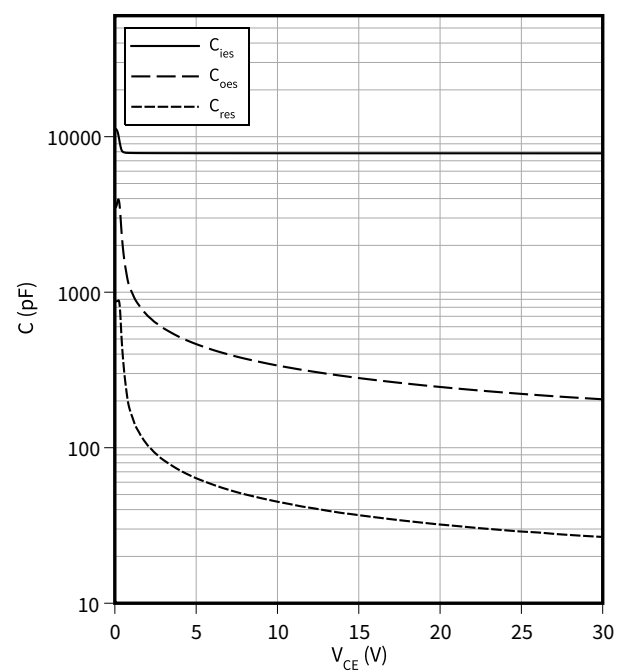
$I_C = 150\text{ A}$



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

$f = 100\text{ kHz}, V_{GE} = 0\text{ V}$

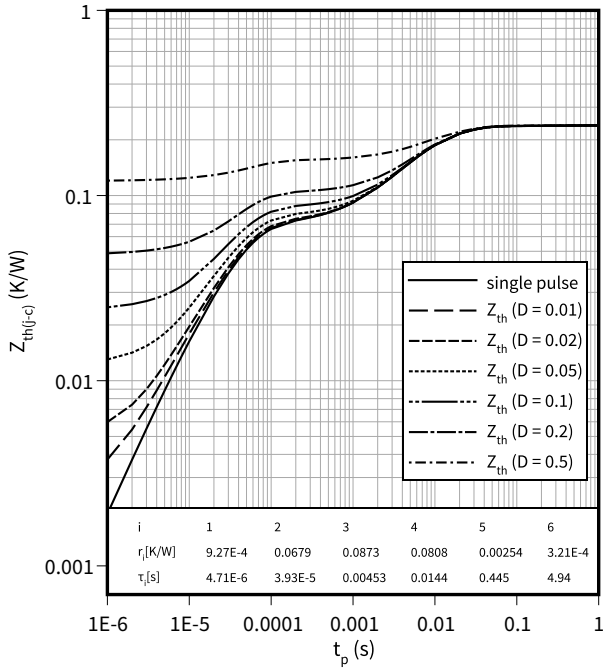


4 Characteristics diagrams

IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

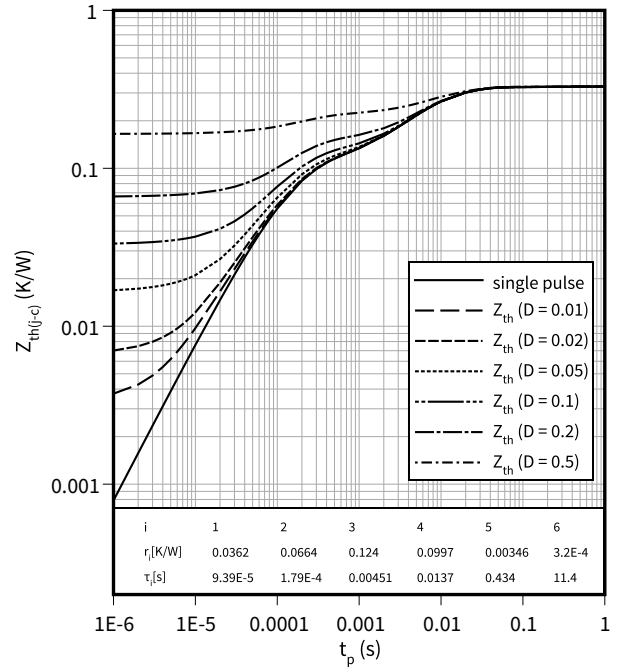
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width

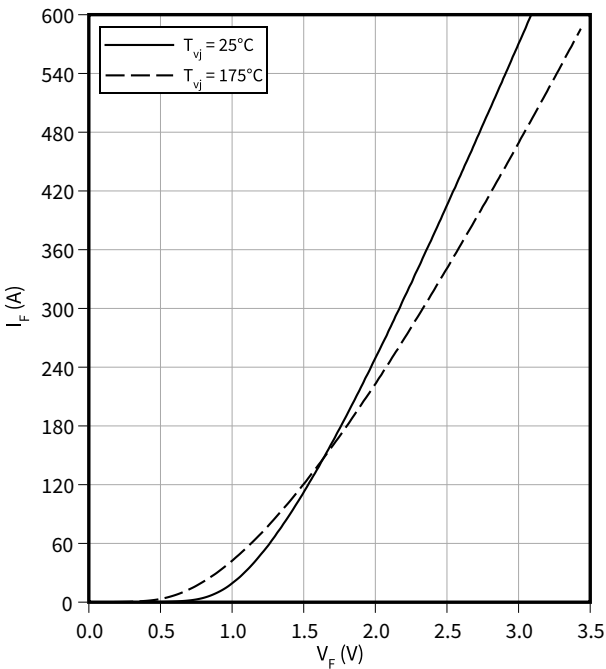
$Z_{th(j-c)} = f(t_p)$

$D = t_p/T$



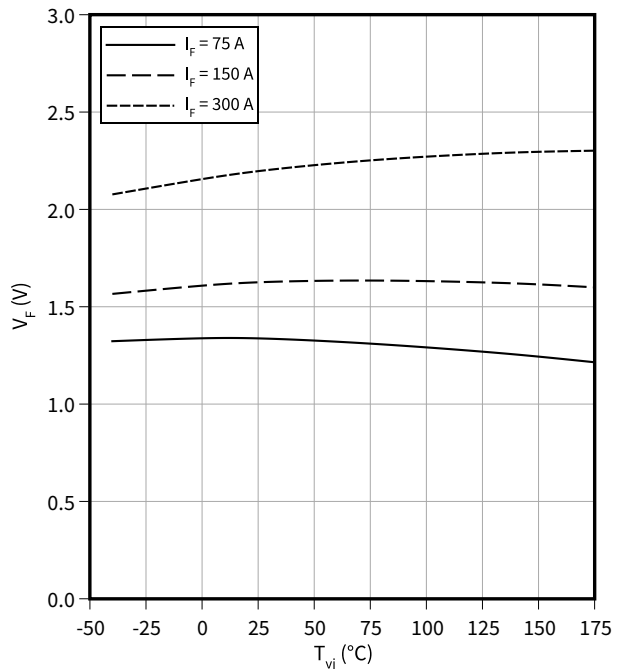
Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature

$V_F = f(T_{vj})$

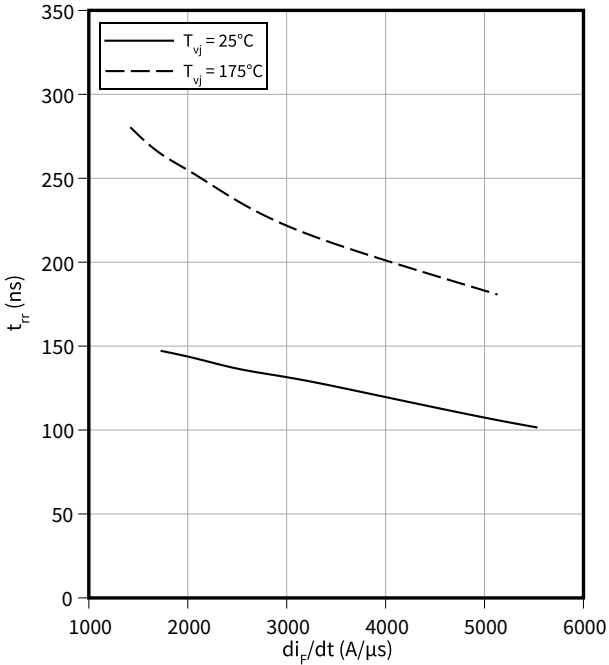


4 Characteristics diagrams

Typical reverse recovery time as a function of diode current slope

$t_{rr} = f(di_F/dt)$

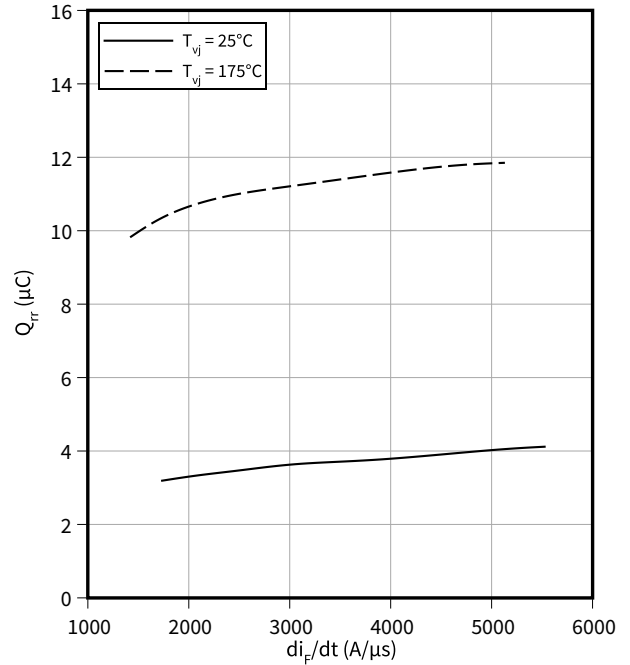
$V_R = 400\text{ V}, I_F = 150\text{ A}$



Typical reverse recovery charge as a function of diode current slope

$Q_{rr} = f(di_F/dt)$

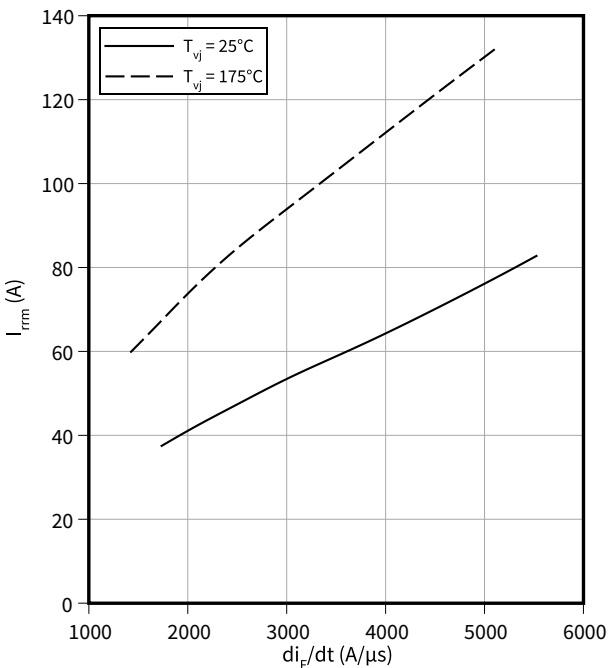
$V_R = 400\text{ V}, I_F = 150\text{ A}$



Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$

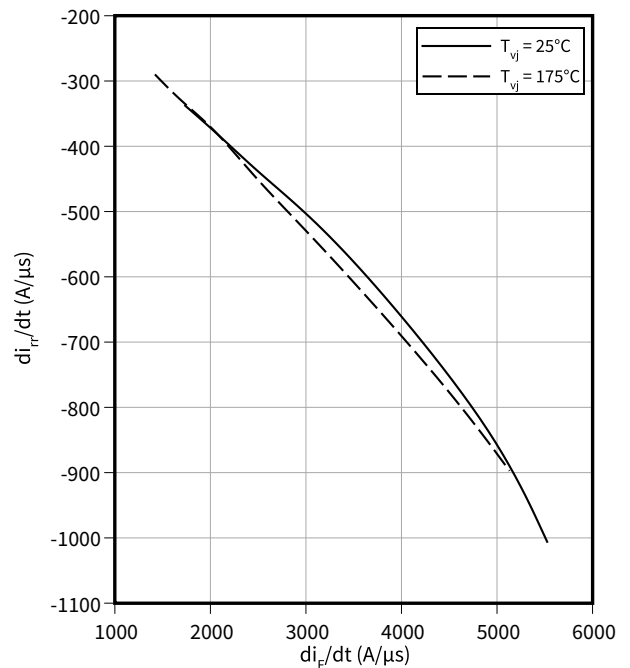
$V_R = 400\text{ V}, I_F = 150\text{ A}$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$

$V_R = 400\text{ V}, I_F = 150\text{ A}$

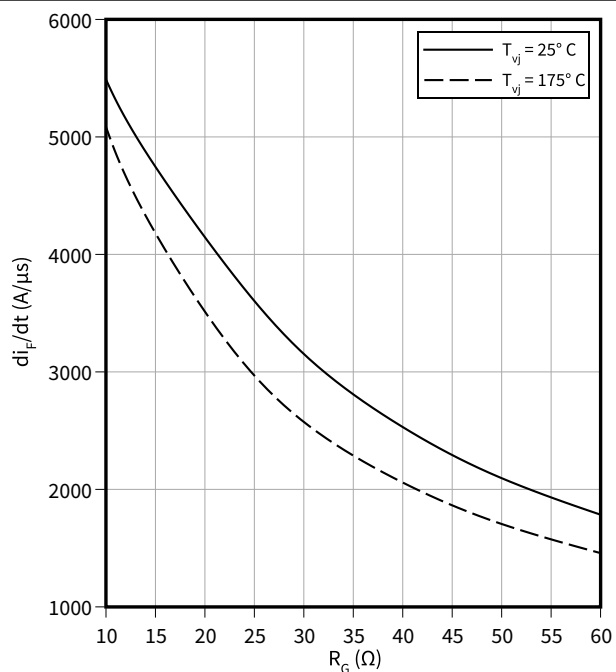


4 Characteristics diagrams

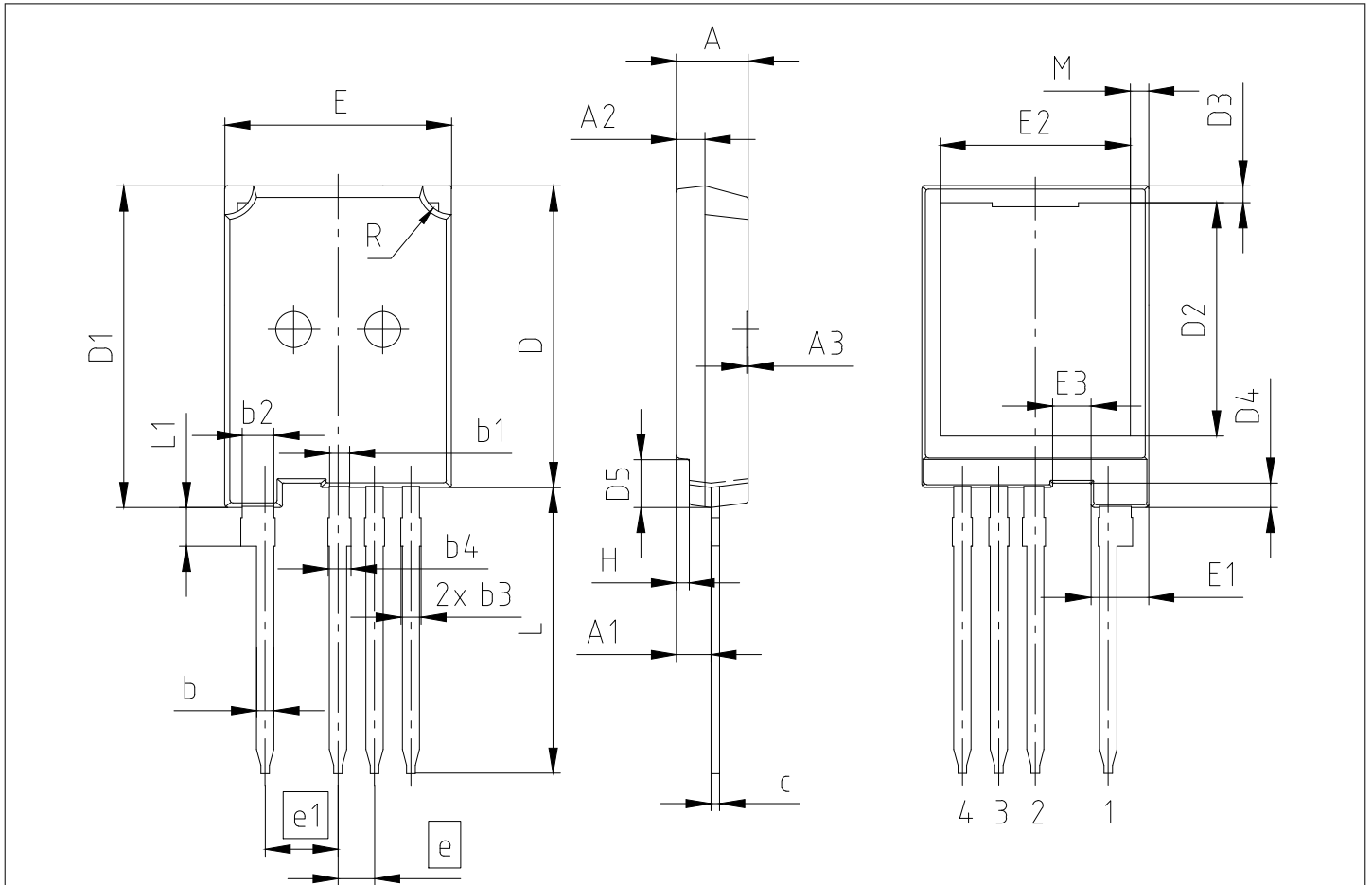
Typical diode current slope as a function of gate resistor

$di_F/dt = f(R_G)$

$V_R = 400\text{ V}, I_F = 150\text{ A}$



5 Package outlines



NOTES:
 PACKAGE SURFACE ROUTE BETWEEN PIN 1 & PIN 2 WILL BE 5.1 mm MIN.
 ALL b... AND c DIMENSIONS INCLUDING PLATING EXPECT AREA OF CUTTING

PACKAGE - GROUP NUMBER:		PG-TO247-4-U10			
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	3.90	4.10
A2	1.90	2.10	E2	13.10	13.50
b	1.16	1.29	E3	2.58	2.78
b1	1.36	1.49	e	2.54	
b2	2.16	2.29	e1	5.08	
b3	1.16	1.45	H	0.80	1.00
b4	1.16	1.65	N	4	
c	0.59	0.66	L	19.80	20.10
D	20.90	21.10	L1	2.55	2.85
D1	22.30	22.50	M	0.97	1.57
D2	15.95	16.55	R	1.90	2.10
D3	1.00	1.35			
D4	1.60	1.80			
D5	3.24	3.44			

Figure 1

6 Testing conditions



Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2025-06-17	Preliminary datasheet
1.00	2025-07-31	Final datasheet

Trademarks

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Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.